AMENDMENTS TO THE CLAIMS

This listing of Claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1 - 16 (canceled).

Claim 17 (currently amended): A structure of a LED device, the structure comprising:

a LED substrate having a GaP layer thereon; and

a ~~liquid phase epitaxy grown~~ transparent layer grown by a liquid phase epitaxy process having Zn dopants therein on said GaP layer of said LED substrate, ~~wherein~~ said transparent layer is composed of a semiconductor compound ~~different to that of said~~ excluding GaP ~~layer~~.

Claim 18 (canceled).

Claim 19 (currently amended): The structure according to claim 17, wherein said liquid phase epitaxy process utilizes a supersaturated solution comprising metallic antimony (Sb) and indium (In) as a solvent.

Claim 20 (currently amended): The structure according to claim 18, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of a solvent of a supersaturated solution in the liquid phase epitaxy process.

Claim 21 (currently amended): The structure according to claim 19, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of Sb of the supersaturated solution in the liquid phase epitaxy process.

Claim 22 (currently amended): A structure of a LED device, the structure comprising:

a LED substrate having a GaP layer thereon; and

~~an~~ a ~~non-GaP~~ transparent layer composed of a semiconductor compound excluding GaP having Zn dopants therein on said GaP layer formed by a liquid phase epitaxy process using a supersaturated solution.

Claim 23 (currently amended): The structure according to claim 22, wherein said ~~non-GaP~~ transparent layer is formed by liquid phase epitaxy process utilizing a supersaturated solution comprising metallic antimony (Sb) and indium (In) as a solvent.

Claim 24 (previously presented): The structure according to claim 22, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of a solvent of a supersaturated solution in the liquid phase epitaxy process.

Claim 25 (previously presented): The structure according to claim 22, wherein said Zn dopant is in an amount of 1/1000 to 1/10 by weight of Sb of the supersaturated solution in the liquid phase epitaxy process.